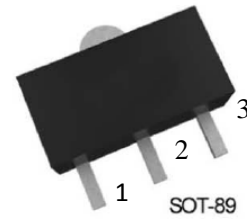


## PNP Silicon Epitaxial Planar Transistor

For switching and amplifier applications.  
Especially suitable for AF-driver stages  
and low power output stages.



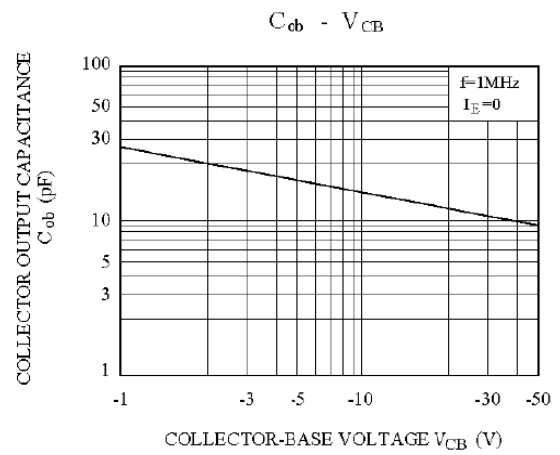
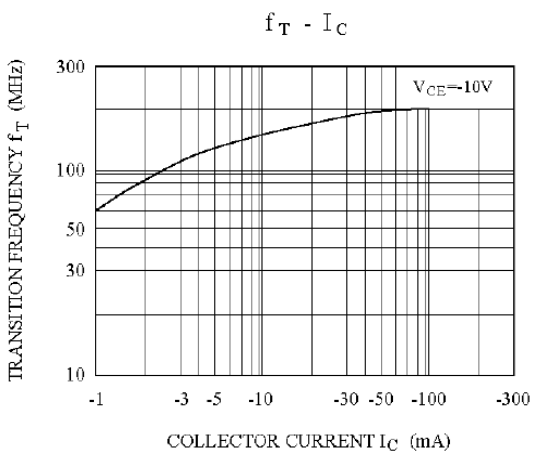
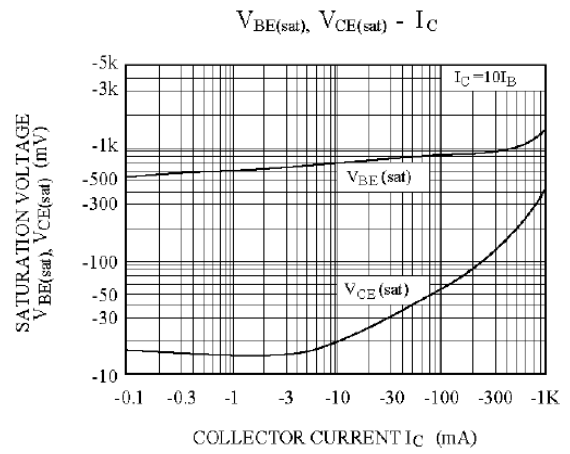
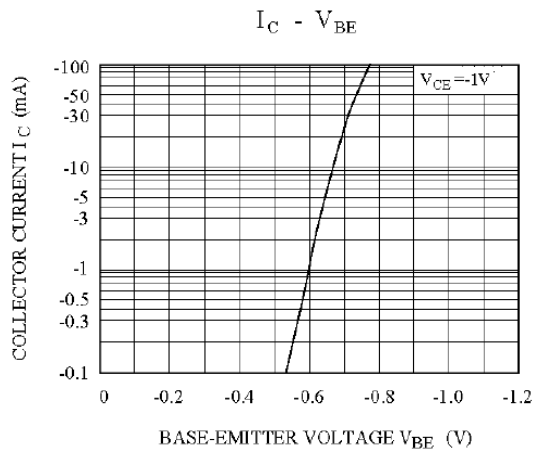
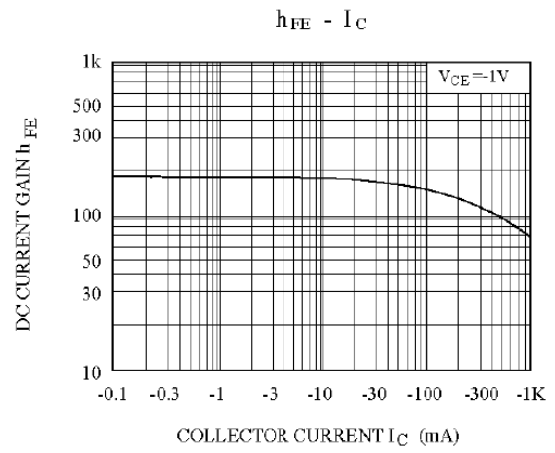
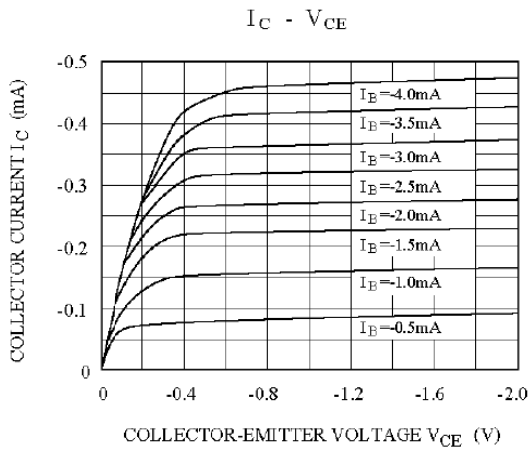
1.Base 2.Collector 3.Emitter  
SOT-89 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

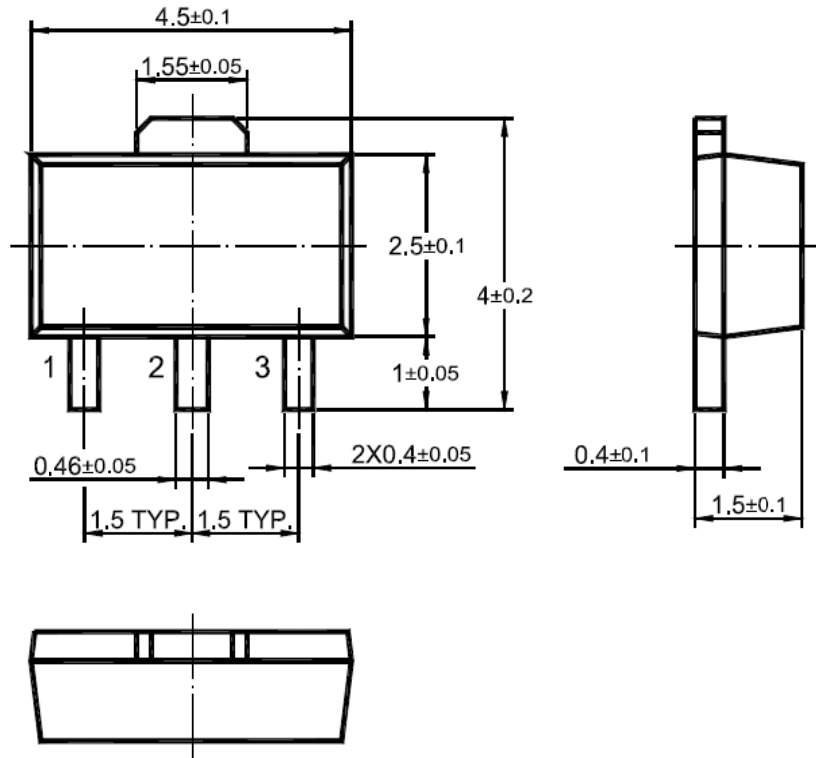
Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CB0}$	40	V
Collector Emitter Voltage	$-V_{CEO}$	25	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	1.5	A
Power Dissipation	$P_{tot}$	625	mW
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{Stg}$	- 55 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain					
at $-V_{CE} = 1\text{ V}$ , $-I_C = 100\text{ mA}$	$h_{FE}$	250	-	350	-
at $-V_{CE} = 1\text{ V}$ , $-I_C = 800\text{ mA}$	$h_{FE}$	40	-	-	-
Collector Base Cutoff Current at $-V_{CB} = 35\text{ V}$	$-I_{CB0}$	-	-	100	nA
Emitter Base Cutoff Current at $-V_{BE} = 5\text{ V}$	$-I_{EBO}$	-	-	100	nA
Collector Base Breakdown Voltage at $-I_C = 100\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	40	-	-	V
Collector Emitter Breakdown Voltage at $-I_C = 2\text{ mA}$	$-V_{(BR)CEO}$	25	-	-	V
Emitter Base Breakdown Voltage at $-I_E = 100\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	5	-	-	V
Collector Emitter Saturation Voltage at $-I_C = 800\text{ mA}$ , $-I_B = 80\text{ mA}$	$-V_{CE(sat)}$	-	-	0.5	V
Base Emitter Saturation Voltage at $-I_C = 800\text{ mA}$ , $-I_B = 80\text{ mA}$	$-V_{BE(sat)}$	-	-	1.2	V
Base Emitter Voltage at $-I_C = 10\text{ mA}$ , $-V_{CE} = 1\text{ V}$	$-V_{BE}$	-	-	1	V
Gain Bandwidth Product at $-V_{CE} = 10\text{ V}$ , $-I_C = 50\text{ mA}$	$f_T$	100	-	-	MHz



SOT-89 PACKAGE OUTLINE



Dimensions in mm